

1 – 2 GHz LOW NOISE AMPLIFIER

- **LOW NOISE**
- **SMALL SIZE**
- **LIGHT WEIGHT**

This wide-band low noise amplifier is intended for use in modern solid state communication and instrumentation equipment, where high reliability microwave signal amplification, high dynamic range are important factors. Typical applications are in satellite or terrestrial telecommunication systems. This microwave LNA is constructed using Gallium Arsenide HEMT amplifier stages of high reliability.

Electrical characteristics:

| | |
|-----------------------------|--|
| Frequency Band * | 1.0 to 2.0 GHz |
| RF Gain | 32 dB |
| Gain Flatness | ± 1 dB |
| Gain Stability | ± 0.5 dB/day max |
| Input Noise Figure | < 1.4 dB |
| I/O Return Loss | 10 dB |
| 1 dB Compression | + 10 dBm |
| I/O Impedance | 50 ohms |
| Supply Voltage | + 12 to 15 V DC |
| RF Connectors | SMA - female |
| Operating Temperature Range | 0 ...+ 60 °C (optional: - 30 ...+ 70 °C) |

Specifications are subject to change without notice.

Outline dimensions (mm):

